TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIV)

TPCA8024

Lithium-Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance: $RDS(ON) = 3.5 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 72 \text{ S (typ.)}$
- Low leakage current: $IDSS = 10 \mu A (max) (VDS = 30 V)$
- Enhancement mode: $V_{th} = 1.3$ to 2.5 V ($V_{DS} = 10$ V, $I_{D} = 1$ mA)

Absolute Maximum Ratings (Ta = 25°C)

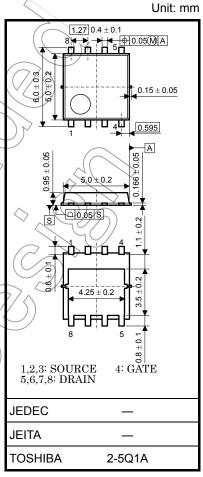
Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	30	> V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	ID <	35	A	
	Pulse (Note 1)	I _{DP}	105		
Drain power dissipation	on (Tc=25°C)	PD (35	W	
Drain power dissipation $(t = 10 s)$ (Note 2a)		PD	2.8	w	
Drain power dissipation	on (t = 10 s) (Note 2b)	PD	1.6	W	
Single pulse avalanch	ne energy (Note 3)	EAS	159	mJ	
Avalanche current		IAR	35	Α	
Repetitive avalanche energy ((Tc=25°C) (Note 4)		E _{AR}	3.5	mJ	
Channel temperature		Tch	150	°C	
Storage temperature range		Tstg	-55 to 150	°C	

Note: For Note 1 to 4, refer to the next page

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor

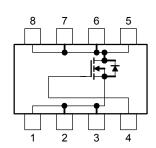
Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

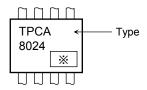
Circuit Configuration



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R _{th (ch-c)}	3.57	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W

Marking (Note 5)

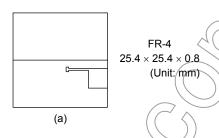


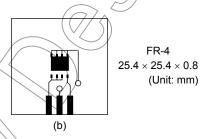
Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2:

(a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

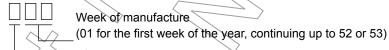




Note 3: $V_{DD} = 24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 0.1 mH, $R_G = 25 \Omega$, $A_R = 35 \text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel/temperature

Note 5: * Weekly code: (Three digits)



Year of manufacture (The last digit of the year)

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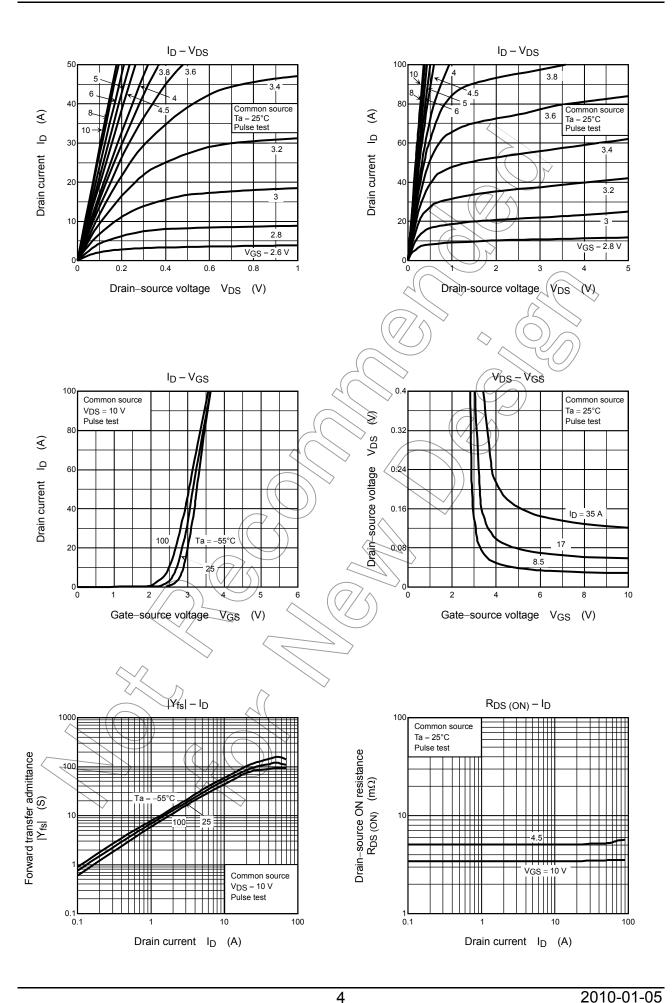
Electrical Characteristics (Ta = 25°C)

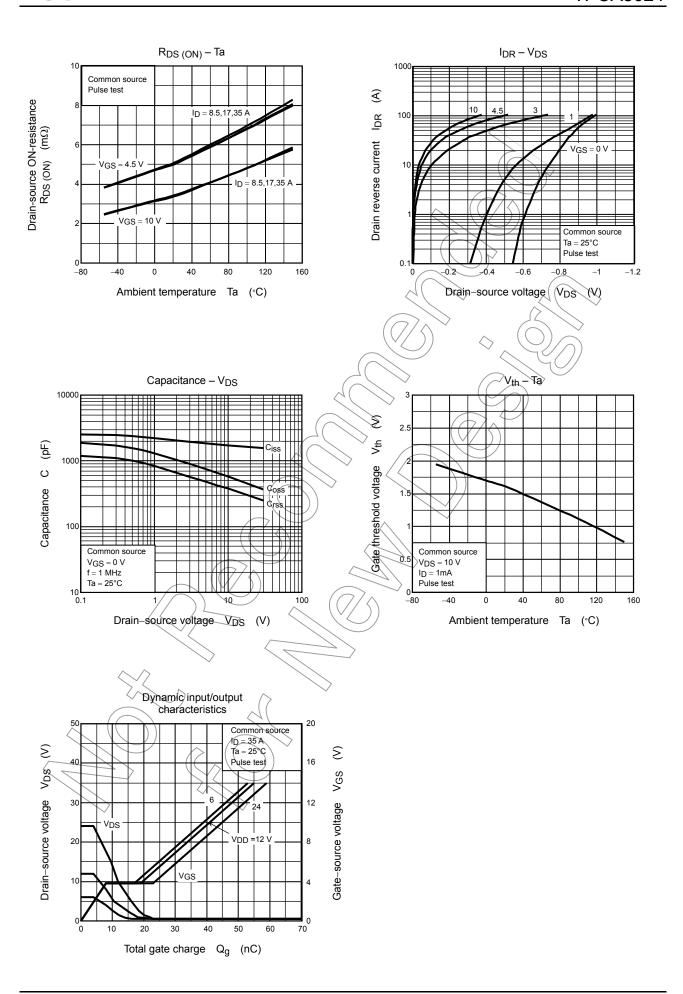
Cha	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cut-OFF cu	rrent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	10	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_		V	
		V _{(BR) DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10				
Gate threshold vo	oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	1.3) /~	2.5	V	
Drain-source ON-resistance		Dec (c)	$V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$		5.4	7.8	- mΩ	
		R _{DS} (ON)	V _{GS} = 10 V, I _D = 17 A	\rightarrow	3.5	4.3		
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 17 A	36	72		S	
Input capacitance		C _{iss}		<u> </u>	1800			
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	370	/	pF	
Output capacitance		Coss		_ /	570	<i>></i>		
Switching time	Rise time	t _r	V _{GS} 10 V	10 V TY ID # 17 A	11	>		
	Turn-on time	t _{on}			19	_	ns	
	Fall time	t _f		(\mathcal{D})	22	_		
	Turn-off time	t _{off}	V _{DD} ≈ 15 V Duty ≤ 1%, t _w = 10 μts) —	64	_		
Total gate charge (gate-source plus		Qg	V _{DD} ≈ 24 V, V _{GS} = 10 V,	_	45	_		
Gate-source charge 1		Q _{gs1}	I _D = 35 A		8		nC	
Gate-drain ("miller") charge		Qgd			15			

Source-Drain Ratings and Characteristics (Ta = 25°C)

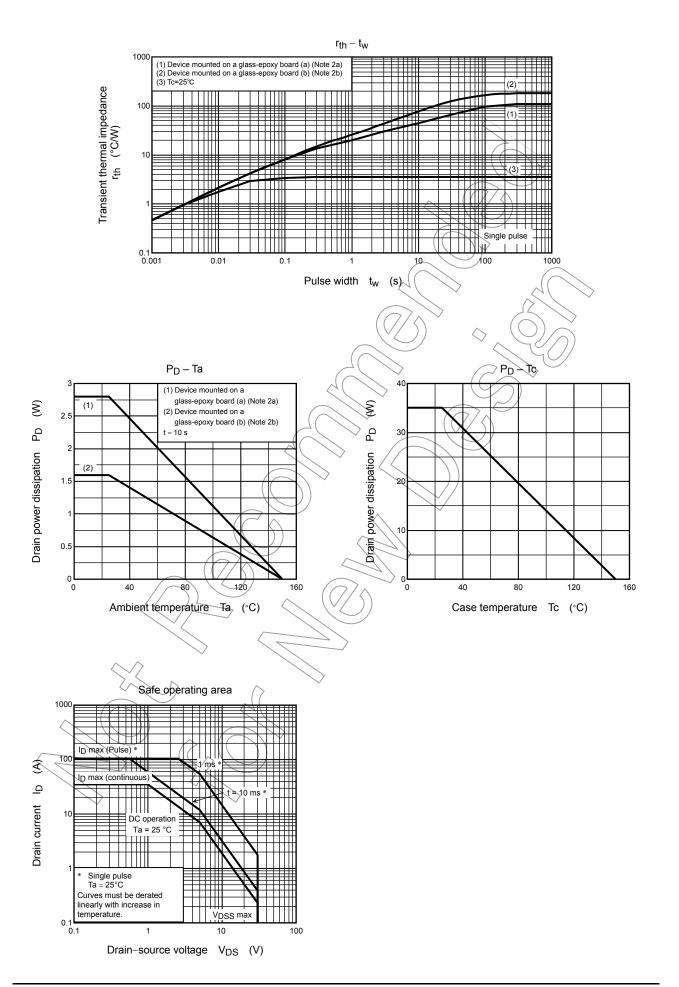
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note-1)	I _{DRP}	/ –	_	_	105	Α
Forward voltage (diode)	VDSE IDR = 35	A, V _{GS} = 0 V	_	_	-1.2	V







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